FFPF30UA60S

Ultrafast II Diode
30 A, 600 V

Description

The FFPF30UA60S is a ultrafast II diode with low forward voltage drop. This device is intended for use as freewheeling and clamping diodes in a variety of switching power supplies and other power switching applications. It is specially suited for use in switching power supplies and industrial application.

Features

- Ultrafast Recovery, t_{RR} = 90 ns (@ I_F = 30 A)
- Max Forward Voltage, V_F = 2.2 V (@ T_C = 25°C)
- 600 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- This Device is Pb−Free and is RoHS Compliant

Applications

- Boost Diode in PFC and SMPS
- Welder, UPS and Motor Control Application

ABSOLUTE MAXIMUM RATINGS

T_C = 25°C unless otherwise noted

| Symbol	Parameter	Rating	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	600	V
V_{RWM}	Working Peak Reverse Voltage	600	V
$I_{F(AV)}$	Average Rectified Forward Current @ T_C = 43°C	30	A
I_{FSM}	Non−repetitive Peak Surge Current 60Hz Single Half−Sine Wave	180	A
T_J, T_{STG}	Operating Junction and Storage Temperature	− 65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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1. Cathode   2. Anode
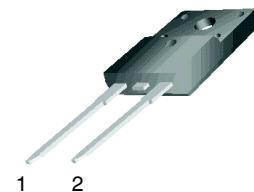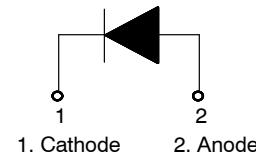
TO−220, 2−Lead
CASE 221AS

MARKING DIAGRAM
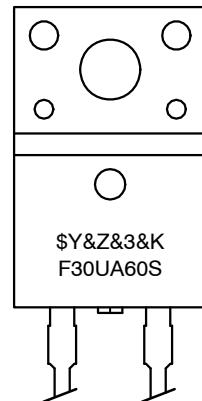
$Y&Z&3&K
F30UA60S

$Y	= ON Semiconductor Logo
&Z&3	= Data Code (Year & Week)
&K	= Lot
F30UA60S	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

THERMAL CHARACTERISTICS $T_C = 25°C$ unless otherwise noted

Symbol	Parameter	Max.	Unit
$R_{\theta JC}$	Maximum Thermal Resistance, Junction to Case	2.5	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFPF30UA60S	F30UA60S	TO−220F−2L	Tube	N/A	N/A	50

ELECTRICAL CHARACTERISTICS $T_C = 25°C$ unless otherwise noted

Parameter	Conditions		Min.	Typ.	Max.	Unit
V_F (Note 1)	$I_F = 30$ A $I_F = 30$ A	$T_C = 25°C$ $T_C = 125°C$	– –	– –	2.2 2.0	V
I_R (Note 1)	$V_R = 600$ V $V_R = 600$ V	$T_C = 25°C$ $T_C = 125°C$	– –	– –	100 150	μA
t_{RR} I_{RR} Q_{RR}	$I_F = 30$ A, $di_F/dt = 200$ A/μs	$T_C = 25°C$	– – –	– – –	90 8 360	ns A nC
W_{AVL}	Avalanche Energy (L = 40 mH)		20	–	–	mJ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
1. Pulse: Test Pulse Width = 300 μs, Duty Cycle = 2%

Test Circuit and Waveforms
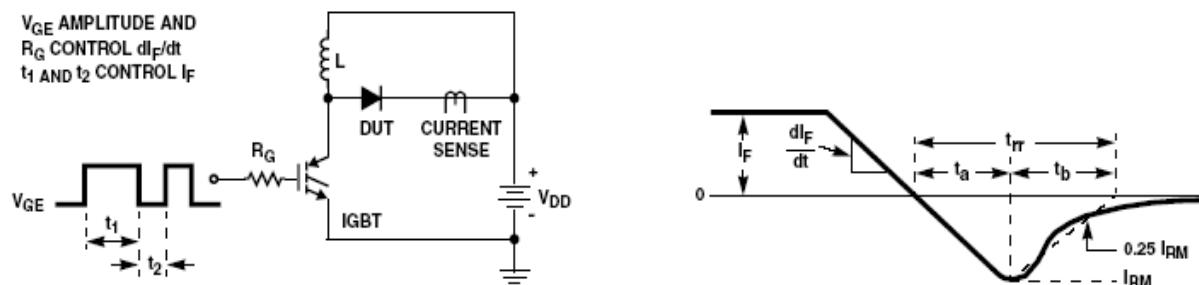
Figure 1. Diode Reverse Recovery Test Circuit & Waveform
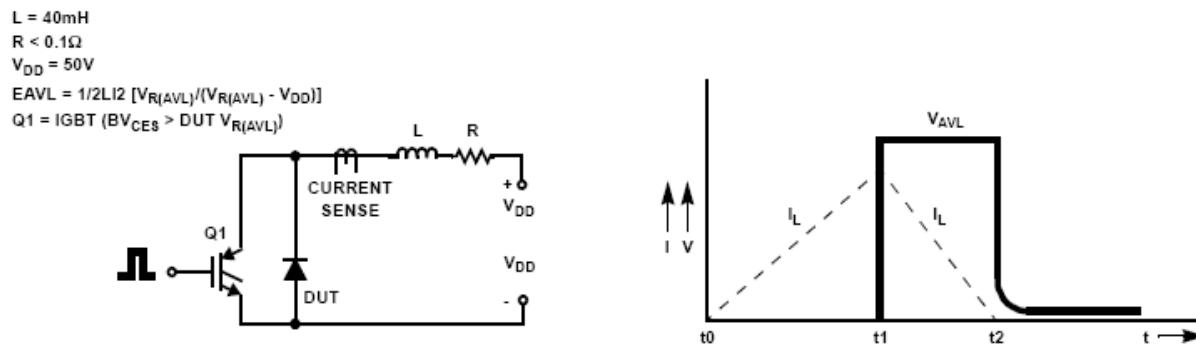
Figure 2. Unclamped Inductive Switching Test Circuit & Waveform

TYPICAL PERFORMANCE CHARACTERISTICS
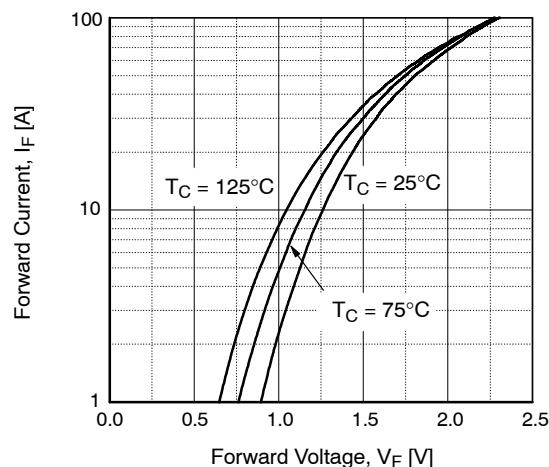
Figure 3. Typical Forward Voltage Drop vs. Forward Current
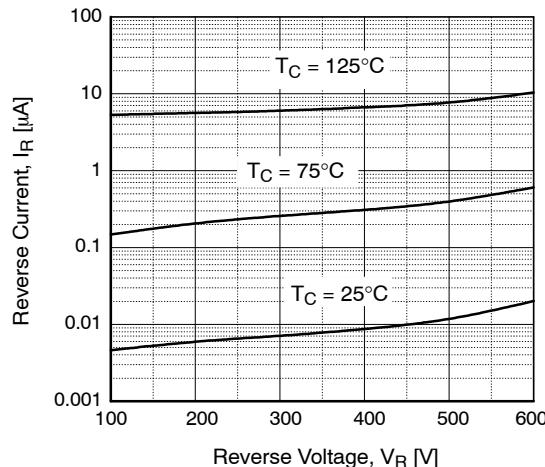
**Figure 4. Typical Reverse Current vs. Reverse Voltage**
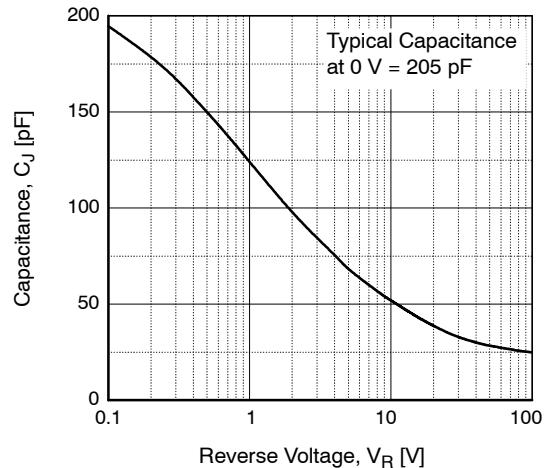
**Figure 5. Typical Junction Capacitance**
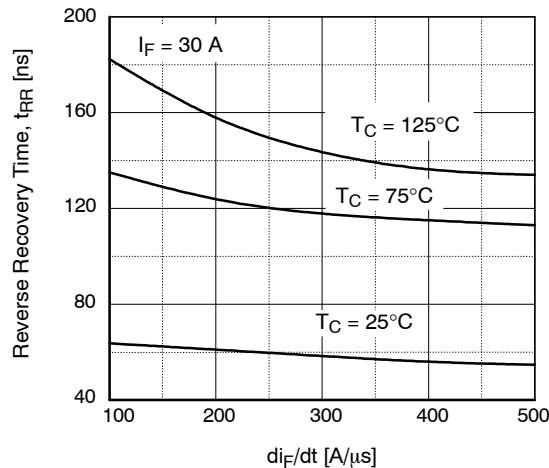
**Figure 6. Typical Reverse Recovery Time vs. di_F/dt**
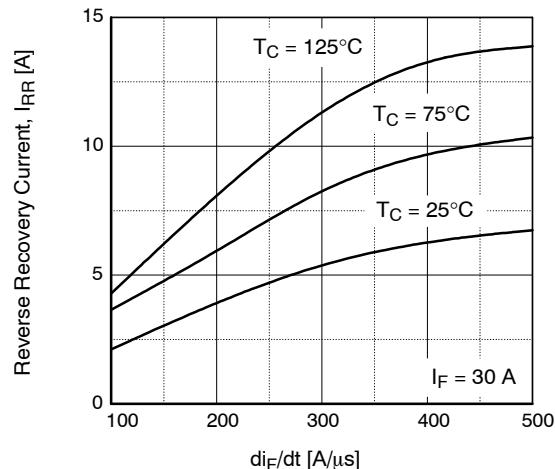
**Figure 7. Typical Reverse Recovery Current vs. di_F/dt**
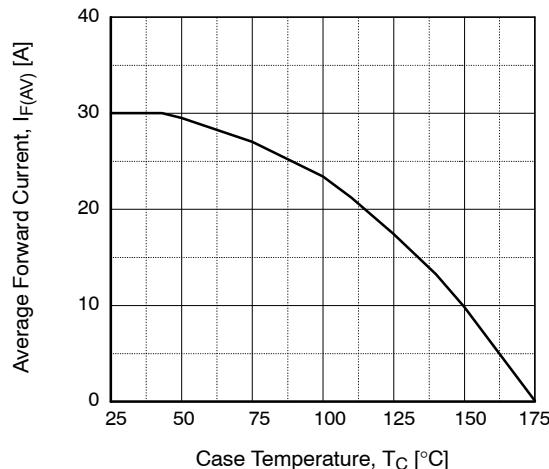
Figure 8. Forward Current Derating Curve

TO−220 Fullpack, 2−Lead / TO−220F−2FS
CASE 221AS
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DATE 29 FEB 2012
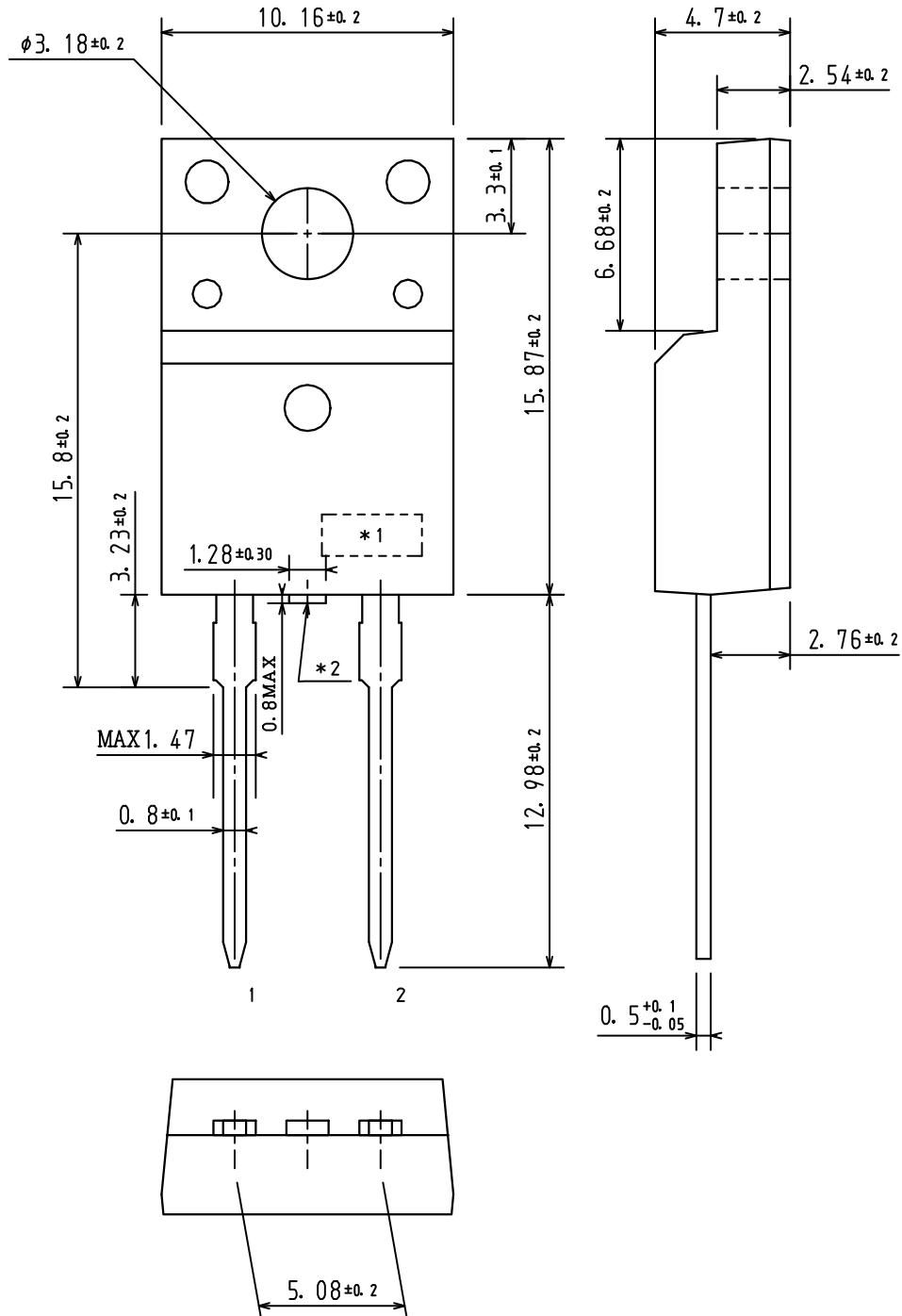
DOCUMENT NUMBER:	98AON67438E		
DESCRIPTION:	**TO−220 FULLPACK, 2−LEAD / TO−220F−2FS**		PAGE 1 OF 1

PUBLICATION ORDERING INFORMATION

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